

Silicon PNP Power Transistors

BDX66

DESCRIPTION

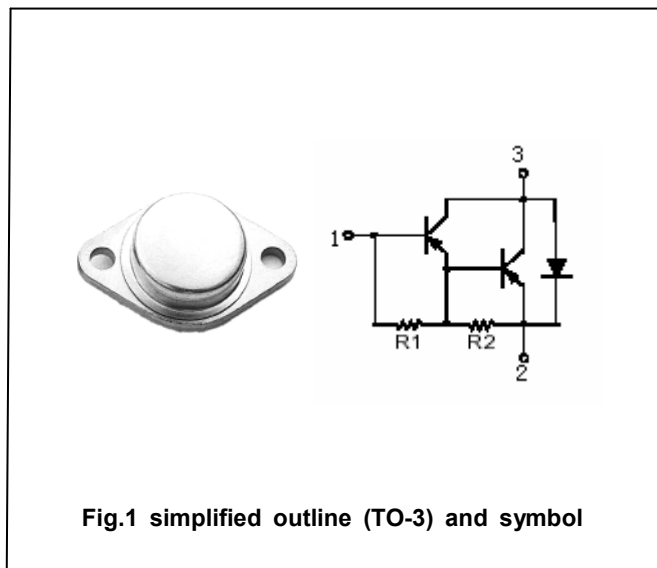
- With TO-3 package
- High current
- DARLINGTON

APPLICATIONS

- Designed for power amplification and switching applications.

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-16	A
I_{CM}	Collector current(peak)		-20	A
I_B	Base current		-0.25	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	150	W
T_j	Junction temperature		-55~200	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.17	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=-0.1\text{A}$; $I_B=0$; $L=25\text{mH}$	-60			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-10\text{A}$; $I_B=-40\text{mA}$			-2	V
I_{CBO}	Collector cut-off current	$V_{CB}=-40\text{V}$; $I_E=0$ $T_C=150^\circ\text{C}$			-1 -5	mA
I_{CEO}	Collector cut-off current	$V_{CE}=-30\text{V}$; $I_B=0$			-3	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5\text{V}$; $I_C=0$			-5	mA

Switching times

t_{on}	Turn-on time	$I_C=-10\text{A}$; $I_{B1}=-I_{B2}=0.04\text{A}$ $V_{CC}=12\text{V}$;		1.0		μs
t_{off}	Turn-off time			3.5		μs

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PACKAGE OUTLINE

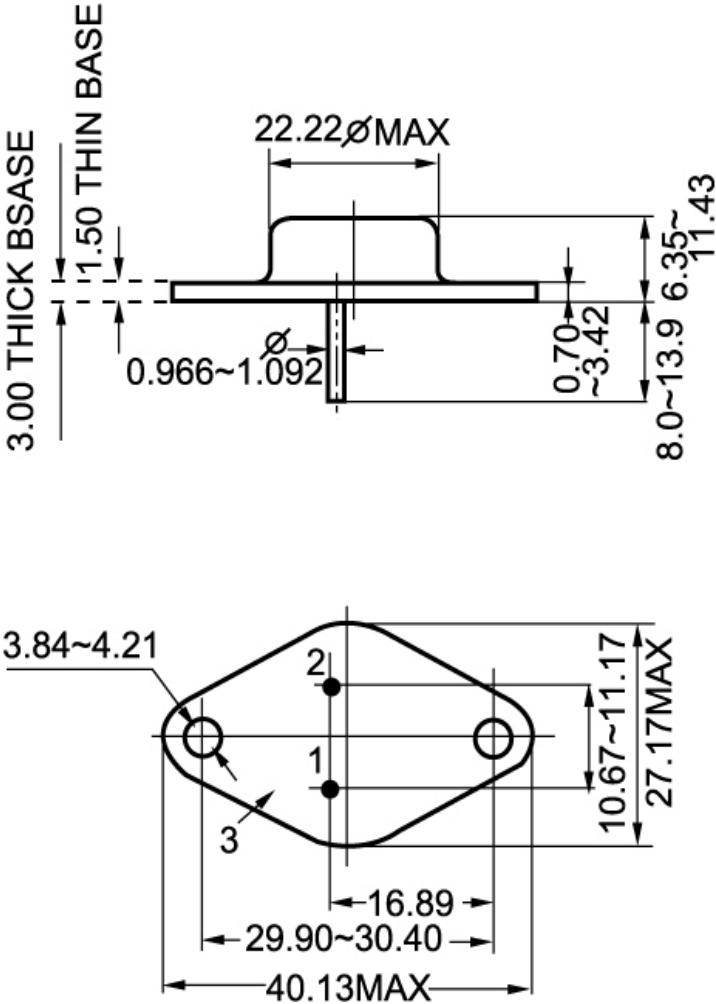


Fig.2 Outline dimensions